

MOSFETs Silicon P-Channel MOS (U-MOSVI)

# TPC8129

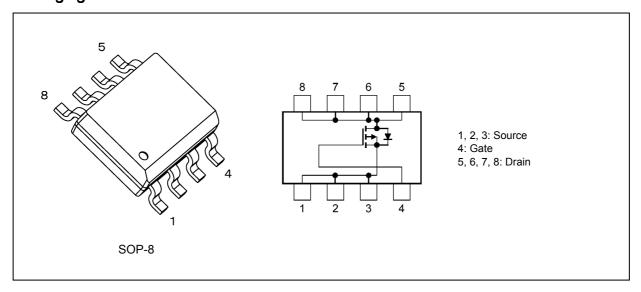
#### Applications

- · Lithium-Ion Secondary Batteries
- · Power Management Switches

#### 2. Features

- (1) Small footprint due to a small and thin package
- (2) Low drain-source on-resistance:  $R_{DS(ON)} = 17 \text{ m}\Omega$  (typ.) ( $V_{GS} = -10 \text{ V}$ )
- (3) Low leakage current:  $I_{DSS} = -10 \mu A \text{ (max) (V}_{DS} = -30 \text{ V)}$
- (4) Enhancement mode:  $V_{th}$  = -0.8 to -2.0 V ( $V_{DS}$  = -10 V,  $I_D$  = -0.2 mA)

#### 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

| Characteri                    | Symbol     | Rating   | Unit             |            |    |
|-------------------------------|------------|----------|------------------|------------|----|
| Drain-source voltage          |            |          | $V_{DSS}$        | -30        | V  |
| Gate-source voltage           |            |          | V <sub>GSS</sub> | -25/+20    |    |
| Drain current (DC)            |            | (Note 1) | I <sub>D</sub>   | -9         | Α  |
| Drain current (pulsed)        |            | (Note 1) | I <sub>DP</sub>  | -36        |    |
| Power dissipation             | (t = 10 s) | (Note 2) | P <sub>D</sub>   | 1.9        | W  |
| Power dissipation             | (t = 10 s) | (Note 3) | $P_{D}$          | 1.0        | W  |
| Single-pulse avalanche energy |            | (Note 4) | E <sub>AS</sub>  | 21         | mJ |
| Avalanche current             |            |          | I <sub>AR</sub>  | -9         | Α  |
| Channel temperature           |            |          | T <sub>ch</sub>  | 150        | °C |
| Storage temperature           |            |          | T <sub>stg</sub> | -55 to 150 |    |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



#### 5. Thermal Characteristics

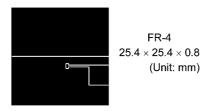
| Characteristics                       |            |          | Symbol                | Max  | Unit |
|---------------------------------------|------------|----------|-----------------------|------|------|
| Channel-to-ambient thermal resistance | (t = 10 s) | (Note 2) | R <sub>th(ch-a)</sub> | 65.7 | °C/W |
| Channel-to-ambient thermal resistance | (t = 10 s) | (Note 3) | R <sub>th(ch-a)</sub> | 125  | °C/W |

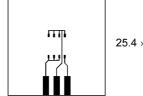
Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4:  $V_{DD}$  = -24 V,  $T_{ch}$  = 25 °C (initial), L = 0.2 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = -9 A





 $\begin{aligned} & \text{FR-4} \\ 25.4 \times 25.4 \times 0.8 \\ & \text{(Unit: mm)} \end{aligned}$ 

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                         | Symbol               | Test Condition                                    | Min  | Тур. | Max  | Unit |
|---|----------------------|---|------|------|------|------|
| Gate leakage current                    | I <sub>GSS</sub>     | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _    | _    | ±0.1 | μА   |
| Drain cut-off current                   | I <sub>DSS</sub>     | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$    | _    |      | -10  |      |
| Drain-source breakdown voltage          | V <sub>(BR)DSS</sub> | I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V    | -30  |      |      | ٧    |
| Drain-source breakdown voltage (Note 5) | V <sub>(BR)DSX</sub> | I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 10 V   | -21  | _    | _    |      |
| Gate threshold voltage                  | $V_{th}$             | $V_{DS} = -10 \text{ V}, I_{D} = -0.2 \text{ mA}$ | -0.8 | _    | -2.0 |      |
| Drain-source on-resistance              | R <sub>DS(ON)</sub>  | $V_{GS} = -4.5 \text{ V}, I_D = -4.5 \text{ A}$   | _    | 22   | 28   | mΩ   |
|   |                      | $V_{GS} = -10 \text{ V}, I_D = -4.5 \text{ A}$    | _    | 17   | 22   |      |

Note 5: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

## 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                | Symbol           | Test Condition  | Min | Тур. | Max | Unit |
|--------------------------------|------------------|---|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 1650 | _   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> |   | _   | 260  | _   |      |
| Output capacitance             | C <sub>oss</sub> |   | _   | 300  | _   |      |
| Switching time (rise time)     | t <sub>r</sub>   | See Fig. 6.2.1.   | _   | 8    | _   | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  |   | _   | 16   | _   |      |
| Switching time (fall time)     | t <sub>f</sub>   |   | _   | 42   | _   |      |
| Switching time (turn-off time) | t <sub>off</sub> |   | _   | 140  | _   |      |

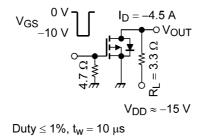


Fig. 6.2.1 Switching Time Test Circuit

## 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                                 | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | $V_{DD} \approx -24 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -9 \text{ A}$ | _   | 39   | _   | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |  | _   | 4    | _   |      |
| Gate-drain charge                               | $Q_{gd}$         |  | _   | 10   | _   |      |

## 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                |          | Symbol    | Test Condition                                | Min | Тур. | Max | Unit |
|--------------------------------|----------|-----------|---|-----|------|-----|------|
| Reverse drain current (pulsed) | (Note 6) | $I_{DRP}$ | _   | _   | -    | -36 | Α    |
| Diode forward voltage          |          | $V_{DSF}$ | I <sub>DR</sub> = -9 A, V <sub>GS</sub> = 0 V |     | 1    | 1.2 | V    |

Note 6: Ensure that the channel temperature does not exceed 150 °C.



## 7. Marking (Note)

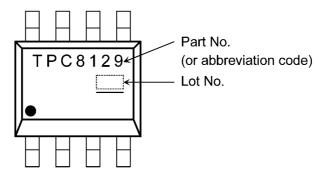


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

### 8. Characteristics Curves (Note)

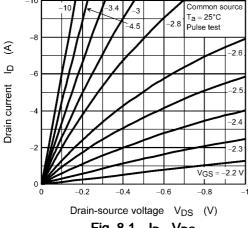
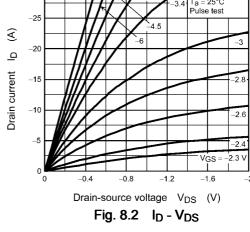


Fig. 8.1  $I_D - V_{DS}$ 



-30

-0.5

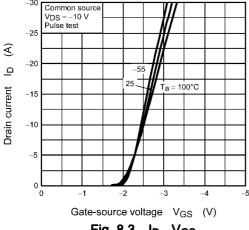


Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

Common source

T<sub>a</sub> = 25°C Pulse test

Drain-source on-resistance RDS(ON)  $(m\Omega)$ 

10

1 L -0.1

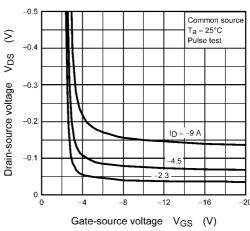
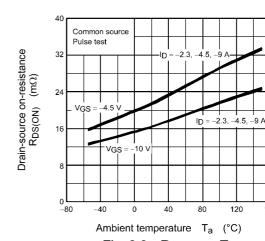


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>



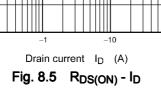


Fig. 8.6 R<sub>DS(ON)</sub> - T<sub>a</sub>

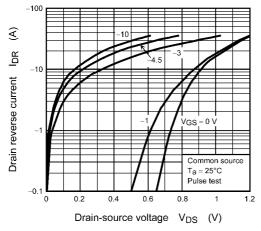


Fig. 8.7 IDR - VDS

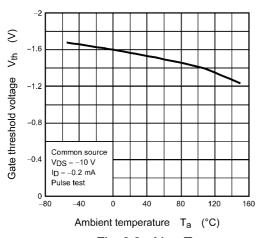


Fig. 8.9 V<sub>th</sub> - T<sub>a</sub>

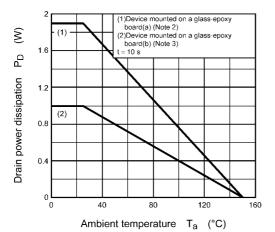


Fig. 8.11 P<sub>D</sub> - T<sub>a</sub> (Guaranteed Maximum)

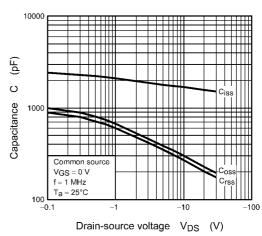


Fig. 8.8 Capacitance - V<sub>DS</sub>

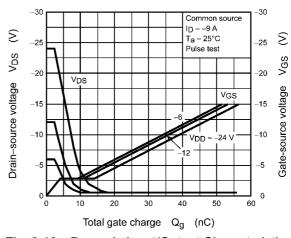


Fig. 8.10 Dynamic Input/Output Characteristics

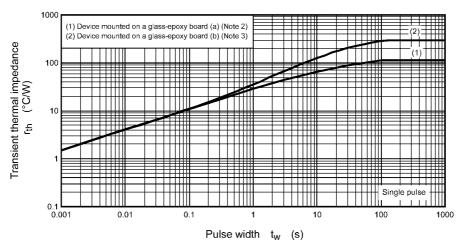


Fig. 8.12 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

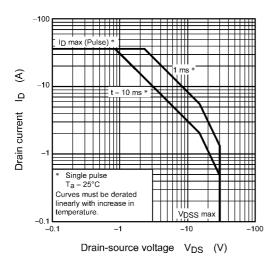


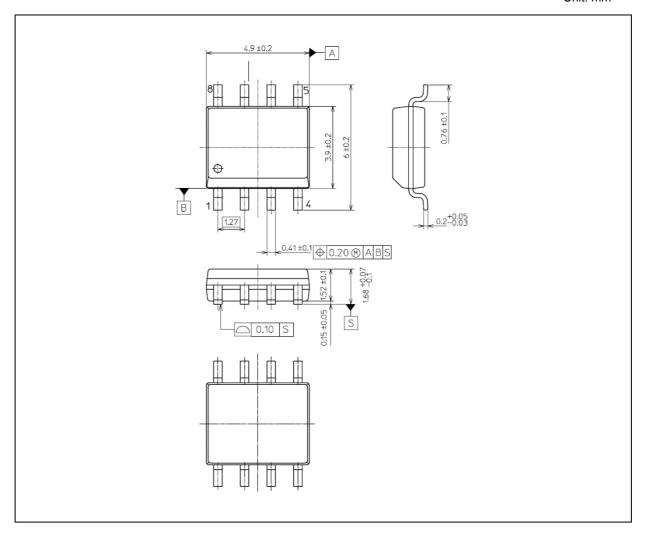
Fig. 8.13 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 0.085 g (typ.)

|                 | Package Name(s) |
|-----------------|-----------------|
| TOSHIBA: 2-5R1S |                 |
| Nickname: SOP-8 |                 |

Rev.2.0



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